

Description

The PSMD2P11R4H uses split gate trench technology to provide excellent $R_{DS(ON)}$ low gate charge. This device is suitable for power management and high efficiency applications at high switching frequencies applications.

MOSFET Product Summary

$V_{DS}(V)$	$R_{DS(on)}(m\Omega)$	$I_D(A)$
100	4.1@ $V_{GS} = 10V$	165

Feature

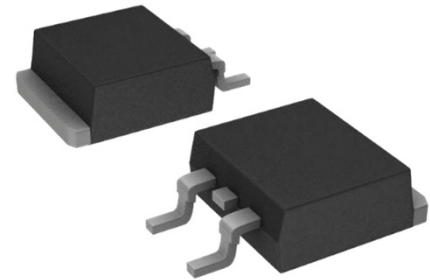
- Low $R_{DS(ON)}$ - Ensures On-State Losses are Minimized
- Excellent $Q_{gd} \times R_{DS(ON)}$ Product(FOM)
- Advanced Technology for DC-DC Converts
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- 100% UIS (Avalanche) Rated
- Lead-Free Finish ; RoHS Compliant
- Halogen and Antimony Free. "Green" Device

Applications

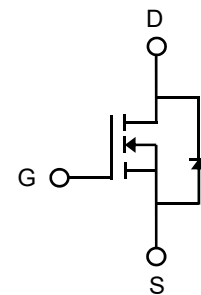
- PWM applications
- Load switch
- Power management
- DC-DC Converters
- Wireless Chargers

Absolute maximum rating@25°C

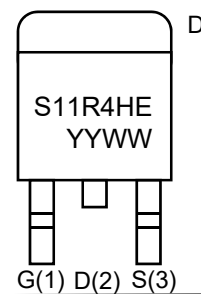
Rating	Symbol	Value	Units
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous ¹⁾	I_D	$T_C=25^\circ C$	165
		$T_C=100^\circ C$	105
Pulsed Drain Current ²⁾	I_{DM}	660	A
Total Power Dissipation ³⁾	P_D	235.8	W
Avalanche Current ⁴⁾	I_{AS}	123	A
Avalanche Energy ⁴⁾	E_{AS}	766	mJ
Thermal Resistance , Junction-case ⁵⁾	$R_{\theta JC}$	0.53	$^\circ C/W$
Thermal Resistance Junction-to-Ambient ⁶⁾	$R_{\theta JA}$	50.3	$^\circ C/W$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^\circ C$



TO-263 (Top View)



Schematic diagram



Marking (Top View)

Electrical characteristics per line@25°C (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	100	113	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$	-	-	1.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	3.2	4.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 50A$	-	4.1	4.5	m Ω
Dynamic Characteristics⁷⁾						
Input Capacitance	C_{iss}	$V_{DS} = 50V, V_{GS} = 0V,$ $f = 1.0MHz$	-	5988	-	pF
Output Capacitance	C_{oss}		-	809	-	
Reverse Transfer Capacitance	C_{rss}		-	28	-	
Switching Characteristics⁷⁾						
Turn-on Delay Time	$t_{d(on)}$	$V_{DS} = 50V, V_{GS} = 10V,$ $R_G = 10\Omega, I_D = 15A$	-	44	-	ns
Turn-on Rise Time	t_r		-	70	-	
Turn-Off Delay Time	$t_{d(off)}$		-	125	-	
Turn-Off Fall Time	t_f		-	70	-	
Total Gate Charge	Q_g	$V_{DS} = 50V, V_{GS} = 10V,$ $I_D = 50A$	-	101	-	nC
Gate-Source Charge	Q_{gs}		-	30	-	
Gate-Drain Charge	Q_{gd}		-	27	-	
Gate Resistance	R_g	$V_{GS}=0V, V_{DS}=0V, f=1MHz$	-	2.1	-	Ω
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = 1A$	-	0.7	1.4	V

Notes:

1. Computed continuous current assumes the condition of $T_{J,Max}$ while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. Repetitive Rating: Pulse width limited by maximum junction temperature($T_{J,Max}=150^\circ C$).
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. This single-pulse measurement was taken under the following condition [$L=100\mu H, V_{GS}=10V, V_{DS}=100V$]while it's value is limited by $T_{J,Max}=150^\circ C$
5. Device mounted on infinite heatsink
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Guaranteed by design, not subject to production

Typical Characteristics

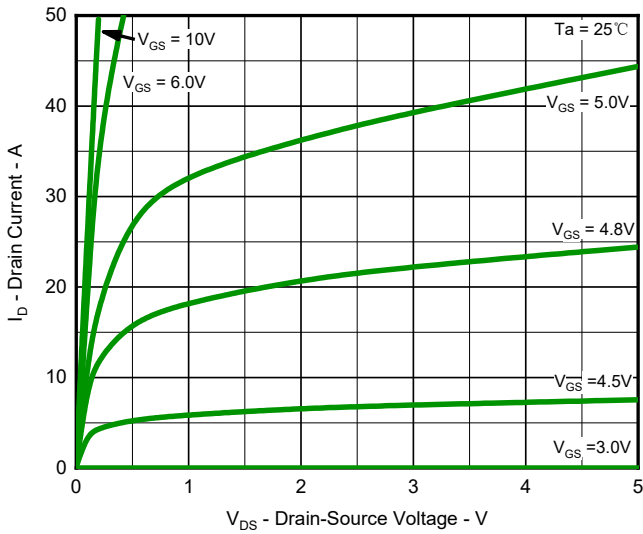


Fig.1 Output Characteristics

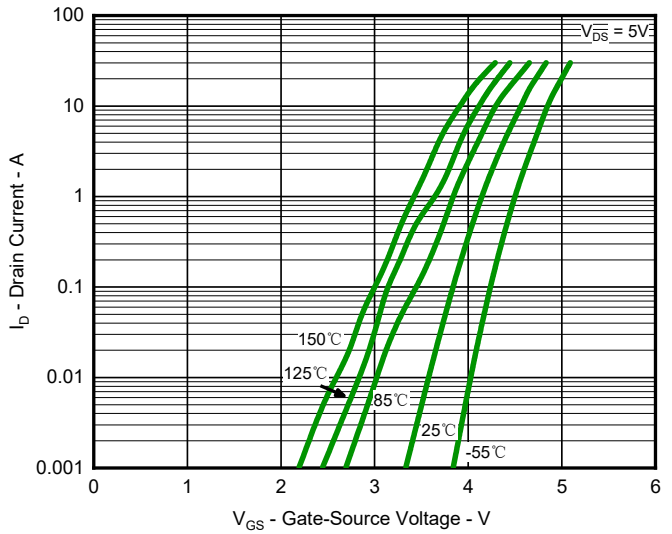


Fig.2 Typical Transfer Characteristic

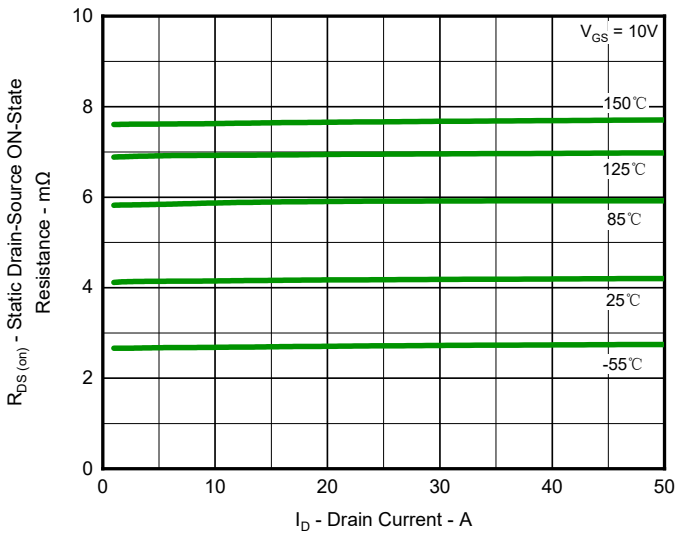


Fig.3 Typical On-Resistance vs Drain Current and Temperature

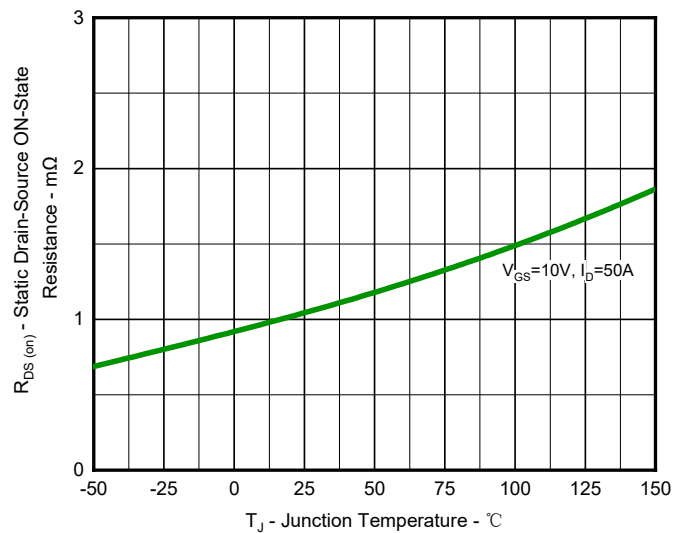


Fig.4 On-Resistance Variation with Temperature

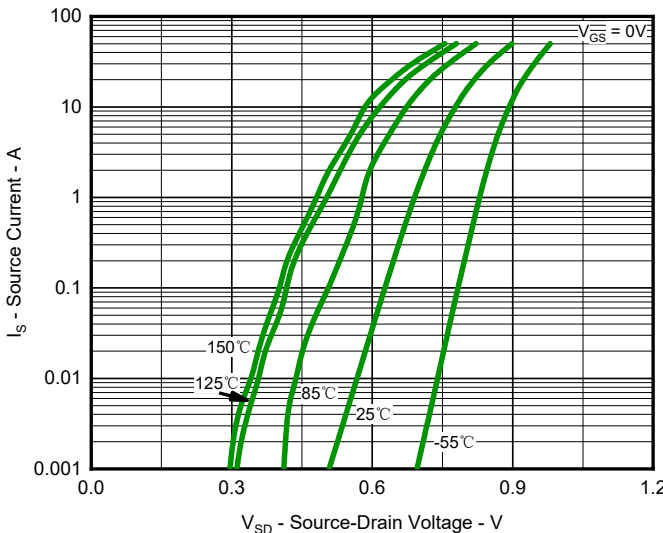


Fig.5 Diode Forward Voltage vs. Current

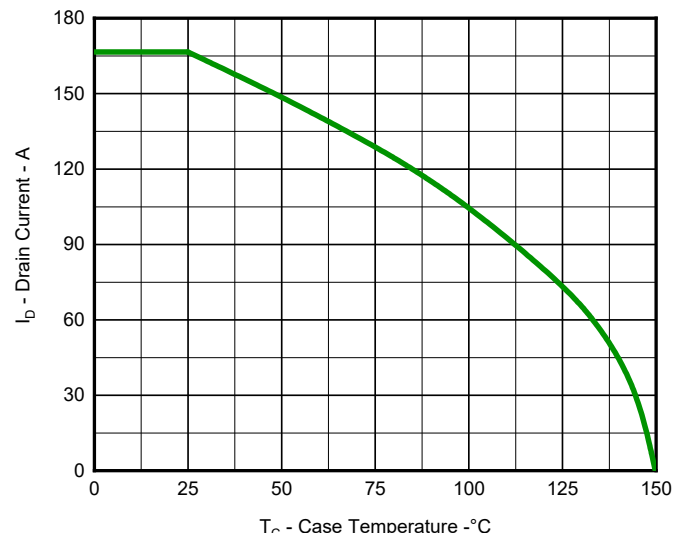


Fig.6 Maximum Drain Current vs. Case Temperature

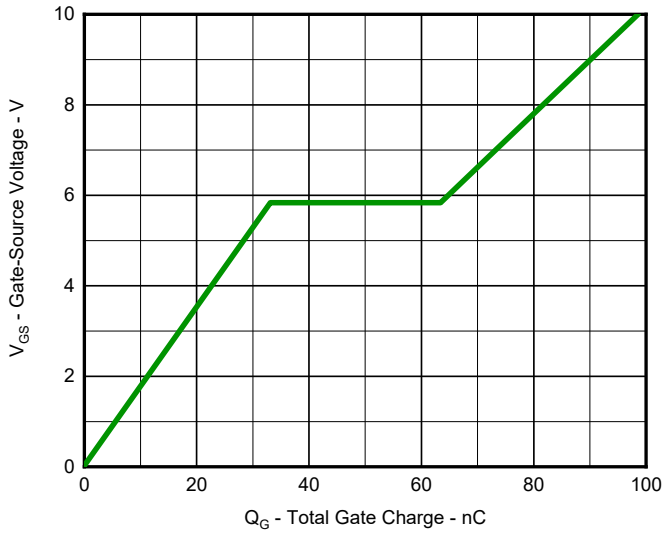


Fig.7 Gate Charge Characteristics

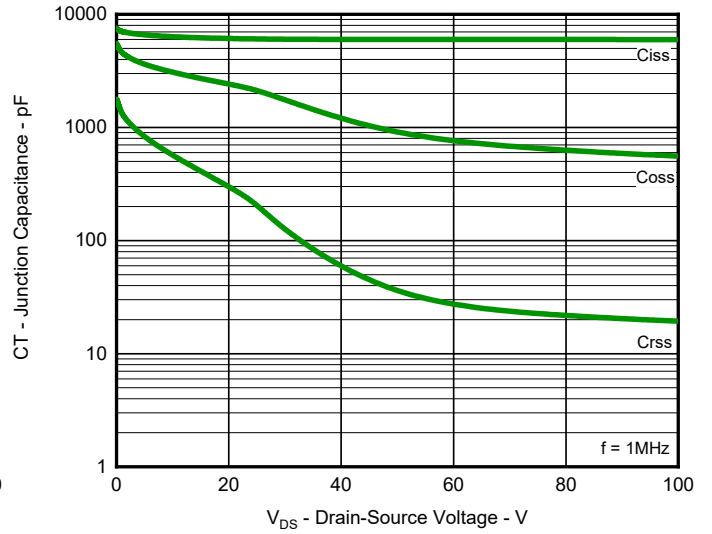


Fig.8 Typical Junction Capacitance

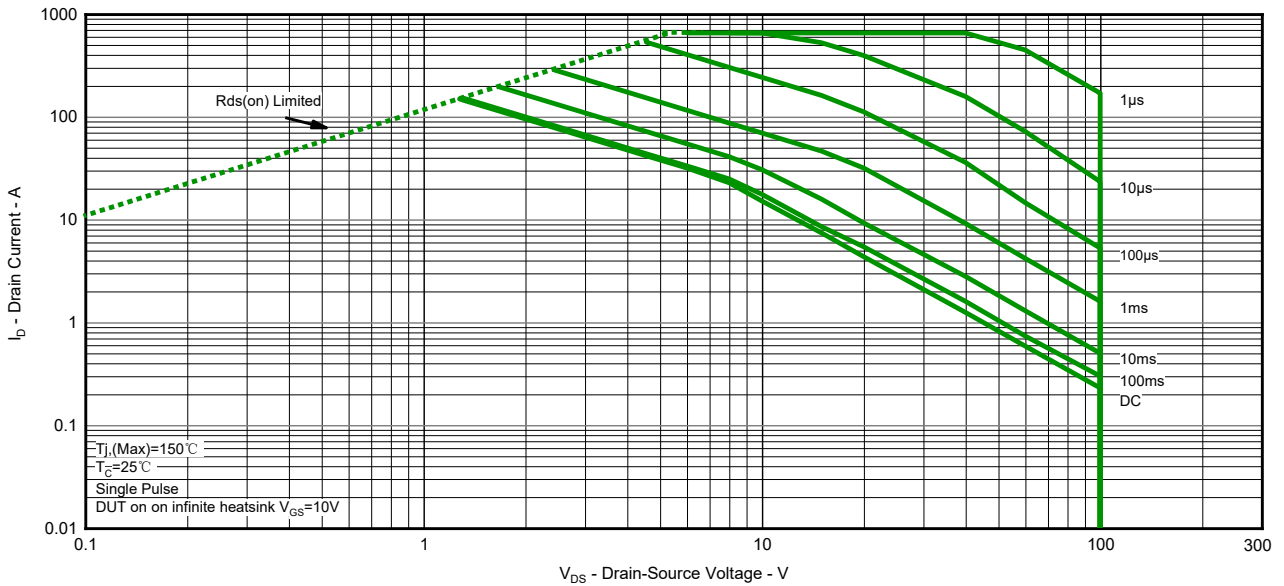


Fig.9 Safe Operation Area

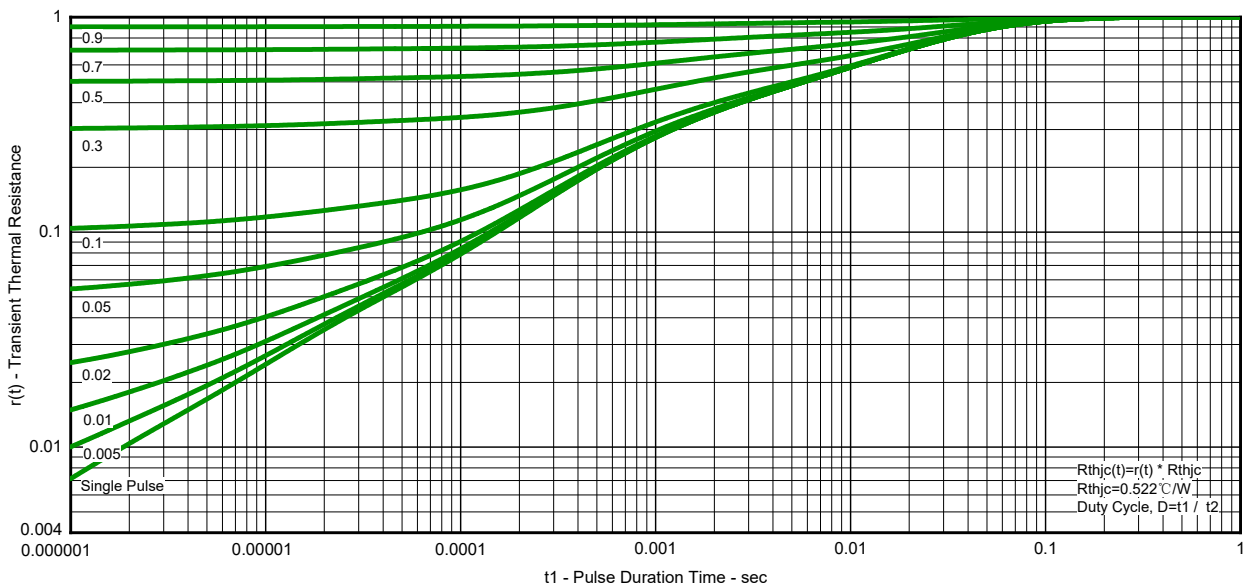
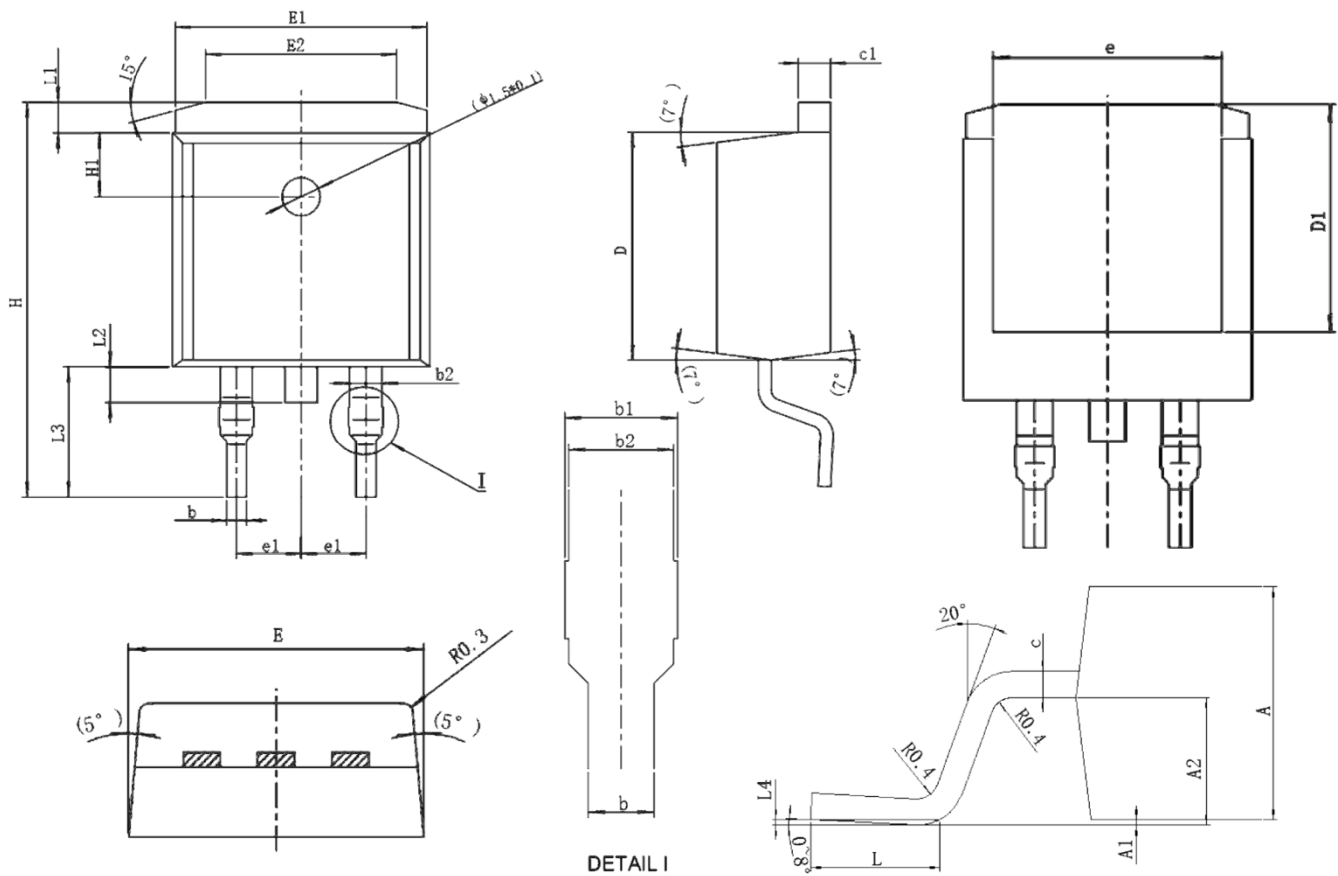


Fig.10 Transient Thermal Resistance

Product dimension (TO-263)



Dim	Millimeters		Inches		Dim	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	4.56	4.58	0.180	0.180	E1	9.85	9.91	0.388	0.390
A1	0.02	0.22	0.001	0.009	E2	7.40	7.60	0.291	0.299
A2	2.34	2.67	0.092	0.105	e	7.50	8.50	0.295	0.335
b	0.75	0.85	0.030	0.033	e1	2.53	2.55	0.100	0.100
b1	1.27	1.47	0.050	0.058	H	15.30	15.70	0.602	0.618
b2	1.22	1.32	0.048	0.052	H1	2.40	2.60	0.094	0.102
c	0.51	0.53	0.020	0.021	L	2.44	2.64	0.096	0.104
c1	1.29	1.32	0.051	0.052	L1	1.10	1.30	0.043	0.051
D	9.14	9.16	0.360	0.361	L2	1.20	1.70	0.047	0.067
D1	7.93	7.95	0.312	0.313	L3	5.14	5.16	0.202	0.203
E	10.00	10.20	0.394	0.402	L4	0.11	0.13	0.004	0.005

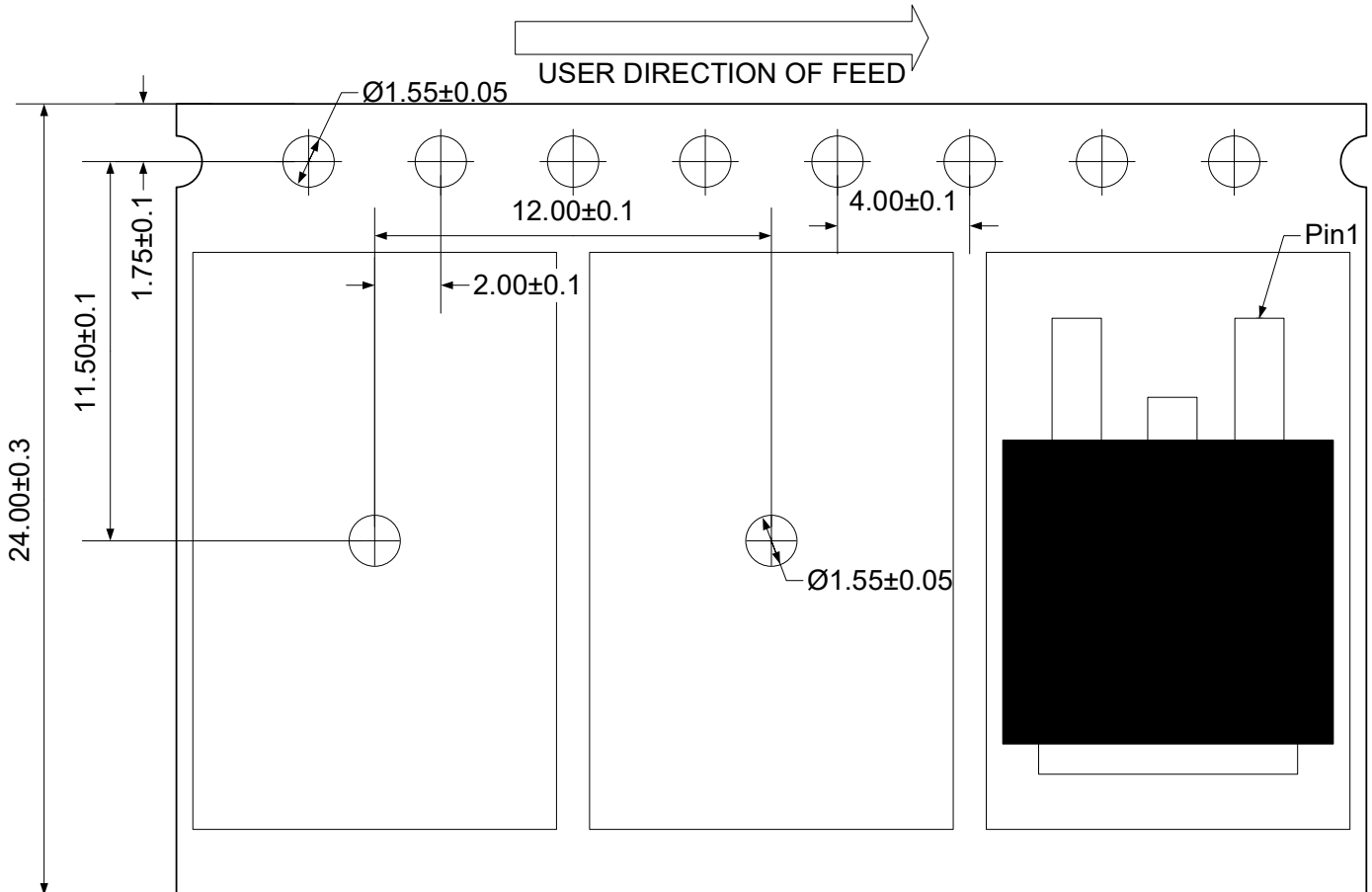
N-Channel MOSFET

PSMD2P11R4H

Ordering Information


Device	Package	Reel	Shipping
PSMTO11R4H	TO-263	13"	800 / Tape & Reel

Load With Information



Unit:mm


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